MTM761230LBF

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Silicon P-channel MOSFET

For Switching

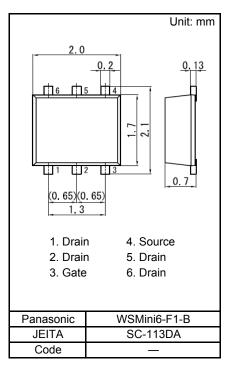
MTM23123 in WSMini6 type package

Features

- Low drain-source ON resistance:RDS(on) typ. = 36 m Ω (VGS = -4.0 V)
- Halogen-free / RoHS compliant
- (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 9C

Packaging

MTM761230LBF Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

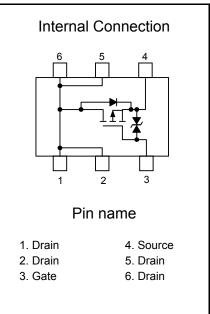


Absolute Maximum Ratings Ta = 25 °C

Symbol	Rating	Unit
VDS	-20	V
VGS	±10	V
ID	-3.0	А
IDp	-16	А
PD	700	mW
Tch	150	°C
Tstg	-55 to +150	°C
	VDS VGS ID IDp PD Tch	VDS -20 VGS ±10 ID -3.0 IDp -16 PD 700 Tch 150

Note: *1 Pulse Width = 10 μ s, Duty Cycle $\leq 1 \%$

*2 Measuring on ceramic board at 40 mm \times 38 mm \times 0.1 mm. PD Absolute maximum rating PD without heat sink shall be made 150 mW.



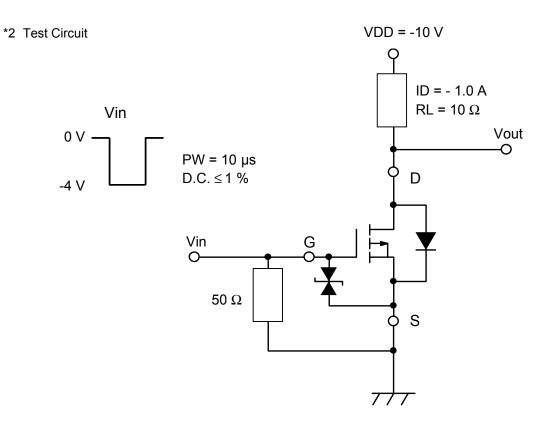
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0 V	-20			V
Zero Gate Voltage Drain Current	IDSS	VDS = -20 V, VGS = 0 V			-1.0	μA
Gate-source Leakage Current	IGSS	VGS = ±8 V, VDS = 0 V			±10	
Gate-source Threshold Voltage	Vth	ID = -1.0 mA, VDS = -10.0 V	-0.4	-0.85	-1.3	V
Drain-source On-state Resistance ^{*1}	RDS(on)1	ID = -1 A, VGS = -4.0 V		36	55	mΩ
	RDS(on)2	ID = -0.5 A, VGS = -2.5 V		42	70	
Forward Transfer Admittance ^{*1}	Yfs	ID = -1.0 A, VDS = -10 V	3.5			S
		f = 1 kHz				
Input Capacitance	Ciss	VDS = -10 V, VGS = 0 V, f = 1 MHz		1000		
Output Capacitance	Coss	VDS = -10 V, VGS = 0 V, f = 1 MHz		100		pF
Reverse Transfer Capacitance	Crss	VDS = -10 V, VGS = 0 V, f = 1 MHz		100		
Turn-on time ^{*2}	ton	VDD = -10 V, VGS = 0 to -4 V		30		ns
		ID = -1 A		30		
Turn-off time ^{*2}	toff	VDD = -10 V, VGS = -4 to 0 V		250		
		ID = -1 A		250		

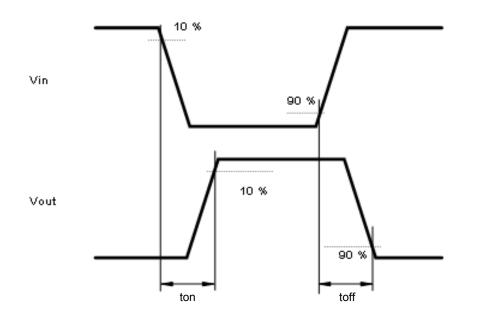
Electrical Characteristics Ta = 25 °C \pm 3 °C

Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

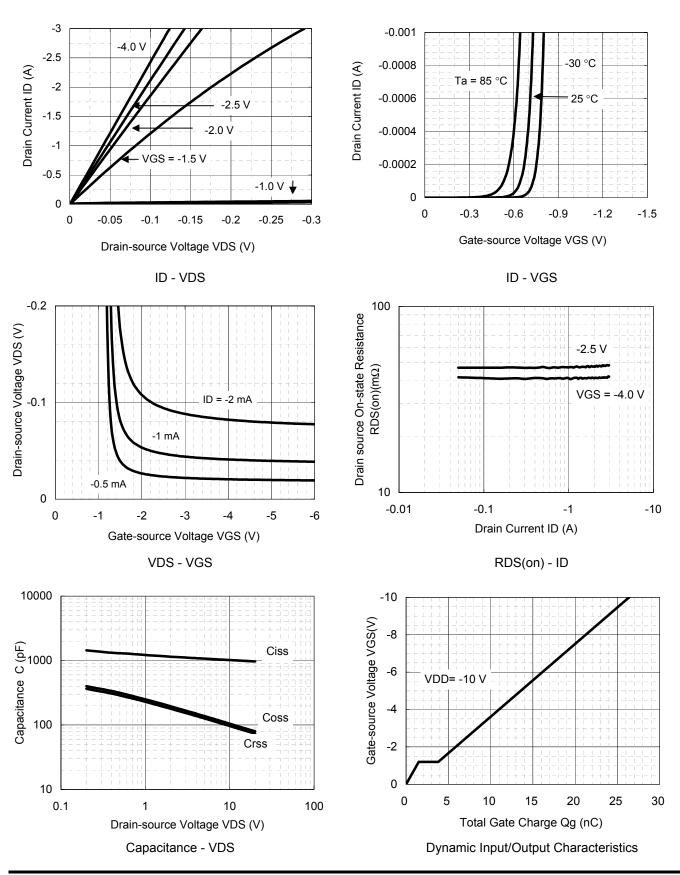
*1 Pulse Test:Pulse Width < 300 μ s, Duty Cycle < 2 %

*2 See Test Circuit





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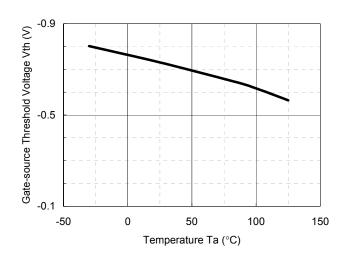
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-2.5 V

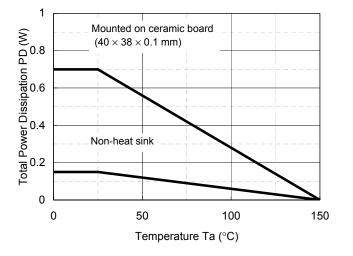
VGS = -4.0 V

150

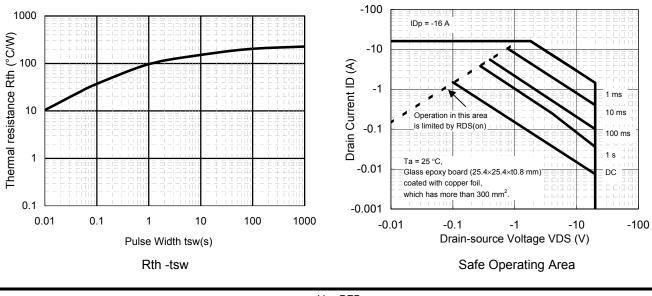
200











80

70 60 50

0

-50

0

50

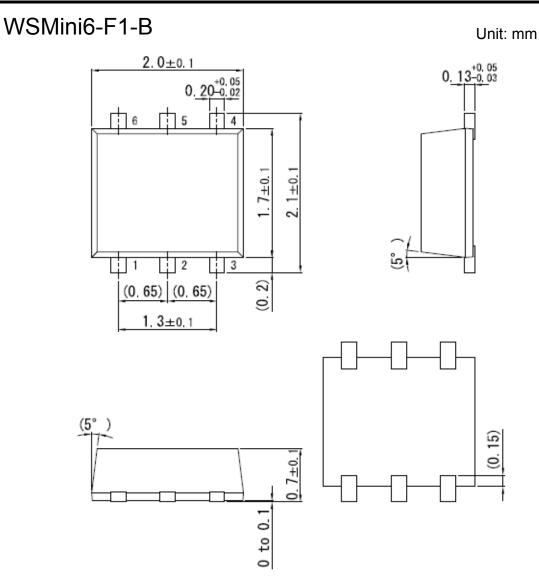
100

Temperature Ta (°C)

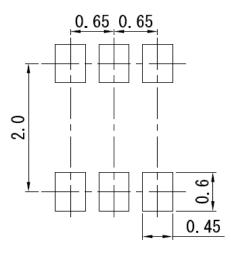
RDS(on) - Ta

Drain-source On-state Resistance RDS(on) (mW)

Ver. DED



■ Land Pattern (Reference) (Unit: mm)



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